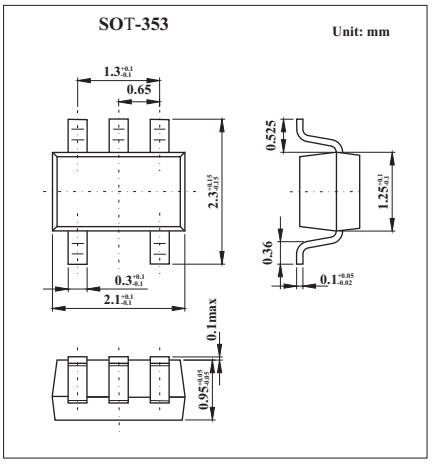
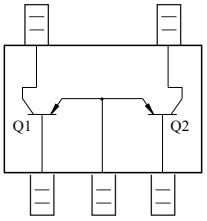
General purpose (Dual PNP Transistors)
KTA501U





Features

Power dissipation: P_C=200mW

Collector Curren: I_C=-150mA

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current -Continuous	I_C	-150	mA
Collector Power Dissipation(TOTAL)	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100μA, I_E=0	-50			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1 mA I_B=0	-50			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100 μA I_C=0	-5.0			V
Collector cutoff current	I_{CBO}	V_{CB}= -50 V , I_E=0			-0.1	μA
Collector cutoff current	I_{EBO}	V_{CE}= -5.0V , I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}= -6V, I_C= -2.0mA	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B= -10mA			-0.3	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -1mA,f=100MHz	80			MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			7	pF
Noise Figure	NF	V_{CE}=-6V, I_C=-0.1mA, f=1KHz , Rg=10KΩ		1	10	dB

h_{FE} Classification

Marking	SY	SGR
Rank	Y	GR
Range	120 240	200 400